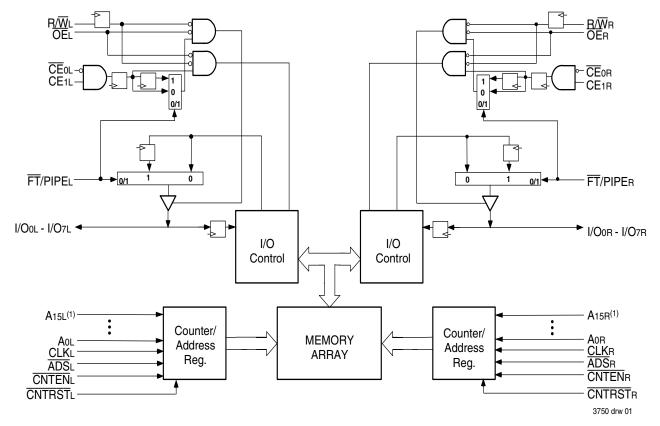
### HIGH-SPEED 3.3V 64/32K x 8 SYNCHRONOUS DUAL-PORT STATIC RAM

### Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
  - Commercial: 7.5ns (max.)
  - Industrial: 12ns (max.)
- Low-power operation
  - IDT70V9089/79L
    - Active:429mW(typ.)
    - Standby: 1.32mW (typ.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pin
- Dual chip enables allow for depth expansion without additional logic

- Counter enable and reset features
   Full synchronous operation on both
  - Full synchronous operation on both ports - 4ns setup to clock and 1ns hold on all control, data, and address inputs
  - Data input, address, and control registers
  - Fast 7.5ns clock to data out in the Pipelined output mode
  - Self-timed write allows fast cycle time
- 12ns cycle time, 83MHz operation in the Pipelined output mode
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Available in a 100 pin Thin Quad Flatpack (TQFP) package
- Green parts available, see ordering information





### NOTE:

1. A15x is a NC for IDT70V9079.

### SEPTEMBER 2019



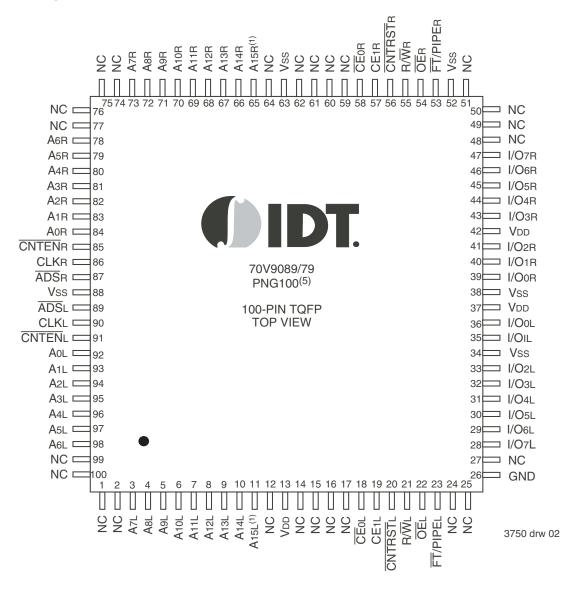
### High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAM

Industrial and Commercial Temperature Range

### Description:

The IDT70V9089/79 is a high-speed 64/32K x 8 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V9089/79 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by  $\overline{CE}_0$  and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using CMOS high-performance technology, these devices typically operate on only 429mW of power.

### Pin Configurations<sup>(2,3,4)</sup>



- 1. A15x is a NC for IDT70V9079.
- 2. All Vcc pins must be connected to power supply.
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm.
- 5. This package code is used to reference the package diagram.

### High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAI

### **Pin Names**

Left Port	Right Port	Names
$\overline{CE}$ OL, CE1L	$\overline{CE}$ OR, CE1R	Chip Enables
R/WL	R/₩R	Read/Write Enable
ŌĒL	<u>OE</u> r	Output Enable
A0L - A15L <sup>(1)</sup>	A0R - A15R <sup>(1)</sup>	Address
I/O0L - I/O7L	I/O0r - I/O7r	Data Input/Output
CLKL	CLKR	Clock
ADSL	ADSR	Address Strobe
	<b>CNTEN</b> R	Counter Enable
<b>CNTRST</b> L	<b>CNTRST</b> R	Counter Reset
<b>FT</b> /PIPEL	<b>FT</b> /PIPER	Flow-Through/Pipeline
V	DD	Power (3.3V)
V	SS	Ground (0V)

3750 tbl 01

## Truth Table I—Read/Write and Enable Control<sup>(1,2,3)</sup>

ŌĒ	CLK		CE1	R∕ <b>₩</b>	I/O0-7	Mode
х	Ŷ	Н	х	х	High-Z	Deselected - Power Down
х	$\uparrow$	х	L	х	High-Z	Deselected - Power Down
х	Ŷ	L	Н	L	DATAIN	Write
L	Ŷ	L	Н	н	DATAOUT	Read
н	х	L	Н	х	High-Z	Outputs Disabled
						3750 tbl 02

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2.  $\overline{ADS}$ ,  $\overline{CNTEN}$ ,  $\overline{CNTRST} = X$ .

3.  $\overline{\text{OE}}$  is an asynchronous input signal.

### Previous Internal External Internal Address MODE ADS I/O<sup>(3)</sup> Address Address Used CLK CNTEN CNTRST ↑ L<sup>(4)</sup> An Х An Х Н Divo (n) External Address Used ↑ L<sup>(5)</sup> An + 1 н н х An Dvo(n+1) Counter Enabled—Internal Address generation $\uparrow$ An + 1 An + 1 н н Dvo(n+1) External Address Blocked—Counter disabled (An + 1 reused) Х н $\uparrow$ L<sup>(4)</sup> Х Х Х х **A**0 Di/O(0) Counter Reset to Address 0

## Truth Table II—Address Counter Control<sup>(1,2,3)</sup>

NOTES:

1.  $\underline{"H"} = VIH, \underline{"L"} = VIL, "X" = Don't Care.$ 

2.  $\overline{CE}_0$  and  $\overline{OE}$  = VIL; CE1 and R/ $\overline{W}$  = VIH.

3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.

4.  $\overline{\text{ADS}}$  and  $\overline{\text{CNTRST}}$  are independent of all other signals including  $\overline{\text{CE}}_0$  and CE1.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CE₀ and CE1.

Industrial and Commercial Temperature Ranges

### NOTE:

- 1. <u>A15x is a NC</u> for IDT70V9079.
- 2.  $\overline{\text{LB}}$  and  $\overline{\text{UB}}$  are single buffered regardless of state of  $\overline{\text{FT}}/\text{PIPE}$ .
- 3.  $\overline{CE}o$  and CE1 are single buffered when  $\overline{FT}/PIPE = V_{IL}$ ,  $\overline{CEo}$  and CE1 are double buffered when  $\overline{FT}/PIPE = V_{IH}$ ,
- i.e. the signals take two cycles to deselect.

### High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RA

### Industrial and Commercial Temperature Range

### Recommended Operating <u>Temperature and Supply Voltage<sup>(1)</sup></u>

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

## Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
VIH	Input High Voltage	2.2		$V_{DD} + 0.3V^{(1)}$	V
Vı∟	Input Low Voltage	-0.3(2)		0.8	V

NOTES:

3750 tbl 04

1. VTERM must not exceed VDD +0.3V.

2. VIL  $\geq$  -1.5V for pulse width less than 10ns.

### Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Commercial & Industrial	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Тѕтс	Storage Temperature	-65 to +150	°C
Tjn	Junction Temperature	+150	°C
Ιουτ	DC Output Current	50	mA
			3750 tbl 06

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

- 2. VTERM must not exceed VDD +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to  $\leq$  20mA for the period of VTERM  $\geq$  VDD + 0.3V.
- 3. Ambient Temperature Under Bias. Chip Deselected.

### Capacitance (TA = +25°C, f = 1.0MHz)

Symbol	Parameter <sup>(1)</sup>	Conditions <sup>(2)</sup>	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Cout <sup>(3)</sup>	Output Capacitance	Vout = 3dV	10	pF
				3750 tbl 07

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static BA

Industrial and Commercial Temperature Range

# DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ( $VDD = 3.3V \pm 0.3V$ )

			70V9089/79S		70V90		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
<b>I</b> ∟ı	Input Leakage Current <sup>(1)</sup>	VDD = 3.3V, VIN = 0V to VDD		10	_	5	μA
llo	Output Leakage Current	$\overline{CE}_0 = V \mathbb{H} \text{ or } CE_1 = V \mathbb{I}, \text{ VOUT} = 0 V \text{ to } V \text{DD}$		10		5	μA
Vol	Output Low Voltage	lol = +4mA		0.4	-	0.4	V
Vон	Output High Voltage	Юн = -4mA	2.4	_	2.4		V

NOTE:

1. At VDD  $\leq$  2.0V input leakages are undefined.

3750 tbl 08

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(6)</sup> (VDD = 3.3V ± 0.3V)

						9/79X6 Only		39/79X7 I Only	70V908 Com'l		
Symbol	Parameter	Test Condition	Versio	on	Typ. <sup>(4)</sup>	Max.	Typ. <sup>(4)</sup>	Max.	Typ. <sup>(4)</sup>	Max.	Unit
Icc	Dynamic Operating Current	$\overline{CE}_{L}$ and $\overline{CE}_{R} = V_{IL}$ Outputs Disabled	COM'L	S L	220 220	395 350	200 200	335 290	180 180	260 225	mA
	(Both Ports Active)	f = fmax <sup>(1)</sup>	IND	S L							
ISB1	Standby Current (Both Ports - TTL	$\overline{CE}L$ and $\overline{CE}R = VIH$ f = fMAX <sup>(1)</sup>	COM'L	S L	70 70	145 130	60 60	115 100	50 50	75 65	mA
	Level Inputs)		IND	S L							
ISB2	Standby Current (One Port - TTL Level Inputs)	$\frac{\overline{CE}}{\overline{CE}} A^{"} = VIL \text{ and } \\ \overline{CE} B^{"} = VIH^{(3)}$	COM'L	S L	150 150	280 250	130 130	240 210	110 110	170 150	mA
		Active Port Outputs Disabled, f=fMAX <sup>(1)</sup>	IND	S L							
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports $\overline{CE}R$ and $\overline{CE}L \ge VDD - 0.2V$	COM'L	S L	1.0 0.4	5 3	1.0 0.4	5 3	1.0 0.4	5 3	mA
	CMOS Level inputs)	$ \begin{array}{l} \mbox{ViN} \geq \mbox{Vdd} \ - \ 0.2 \mbox{V} \ \mbox{or} \\ \mbox{ViN} \leq \ 0.2 \mbox{V}, \ \mbox{f} \ = \ \mbox{0}^{(2)} \\ \end{array} $	IND	S L							
ISB4	Full Standby Current (One Port -	$\frac{\overline{CE}}{\overline{CE}} A^{"} \leq 0.2V \text{ and}$ $\frac{\overline{CE}}{\overline{B}} \geq V DD - 0.2V^{(5)}$	COM'L	S L	140 140	270 240	120 120	230 200	100 100	160 140	mA
	CMOS Level Inputs)	$ \begin{array}{l} \text{VIN} \geq \text{VDD} - 0.2\text{V or} \\ \text{VIN} \leq 0.2\text{V} \text{, Active Port} \\ \text{Outputs Disabled, } f = f_{\text{MAX}}^{(1)} \\ \end{array} $	IND	S L							

3750 tbl 09a

### NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4.  $\underline{V}_{DD}$  = 3.3V, TA =  $\underline{25}^{\circ}C$  for Typ, and are not production tested. ICC DC(f=0) = 90mA (Typ).
- 5.  $\overline{CE}x = VIL$  means  $\overline{CE}_{0X} = VIL$  and  $CE_{1X} = VIH$ 
  - $\overline{CE}x = VIH$  means  $\overline{CE}_{0X} = VIH$  or  $CE_{1X} = VIL$
  - $\overline{CE}x \leq 0.2V$  means  $\overline{CE}_{0}x \leq 0.2V$  and CE1x  $\geq$  VDD 0.2V
  - $\overline{CE}x \ge V_{DD}$  0.2V means  $\overline{CE}_{0X} \ge V_{DD}$  0.2V or CE1x  $\le 0.2V$
- "X" represents "L" for left port or "R" for right port.
- 6. 'X' in part number indicates power rating (S or L).

High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAM

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(6)</sup> ( $VDD = 3.3V \pm 0.3V$ )(Cont'd)

					70V9089 Com'l		70V9089 Com'l		
Symbol	Parameter	Test Condition	Versio	on	Typ. <sup>(4)</sup>	Max.	Typ. <sup>(4)</sup>	Max.	Unit
Icc	Dynamic Operating Current	$\overline{CE}_{L}$ and $\overline{CE}_{R} = V_{IL}$ Outputs Disabled	COM'L	S L	150 150	240 215	130 130	220 185	mA
	(Both Ports Active)	$f = fmax^{(1)}$	IND	S L	150	215			
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}L$ and $\overline{CE}R = VIH$ f = fMAX <sup>(1)</sup>	COM'L	S L	40 40	65 60	30 30	55 35	mA
			IND	S L	40	60			
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{\underline{CE}}^{HA^{H}} = VIL \text{ and } $ $\overline{CE}^{HB^{H}} = VIH^{(3)}$ Active Det Outputs Displayed	COM'L	S L	100 100	160 140	90 90	150 130	mA
		Active Port Outputs Disabled, f=fMAX <sup>(1)</sup>	IND	S L	100	150			
ISB3	Full Standby Current (Both Ports -	Both Ports $\overline{CE}_{R}$ and $\overline{CE}_{L} \ge V DD - 0.2V$	COM'L	S L	1.0 0.4	5 3	1.0 0.4	5 3	mA
	CMOS Level Inputs)	$ \begin{array}{l} \mbox{ViN} \geq \mbox{Vdd} \ - \ 0.2 \mbox{V} \ \mbox{or} \\ \mbox{ViN} \leq \ 0.2 \mbox{V}, \ \mbox{f} \ = \ \mbox{0}^{(2)} \\ \end{array} $	IND	S L	0.4	3			
ISB4	Full Standby Current (One Port -	$\overline{CE}^{"A"} \leq 0.2V \text{ and}$ $\overline{CE}^{"B"} \geq V_{DD} - 0.2V^{(5)}$	COM'L	S L	90 90	150 130	80 80	140 120	mA
	CMOS Level Inputs)	$ \begin{array}{l} \text{VIN} \geq \text{VDD} - 0.2 \text{V or} \\ \text{VIN} \leq 0.2 \text{V}, \text{ Active Port} \\ \text{Outputs Disabled, } f = f_{\text{MAX}}^{(1)} \\ \end{array} $	IND	S L	90	140			

3750 tbl 09b

- 1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4.  $V_{DD} = 3.3V$ , TA = 25°C for Typ, and are not production tested. ICC DC(f=0) = 90mA (Typ).
- 5.  $\overline{CE}x = VIL$  means  $\overline{CE}_{0X} = VIL$  and  $CE_{1X} = VIH$
- $\overline{CE}x = VIH$  means  $\overline{CE}OX = VIH$  or CE1X = VIL
- $\overline{CE}x \leq 0.2V$  means  $\overline{CE}\textsc{ox} \leq 0.2V$  and CE1x  $\geq$  VDD 0.2V
- $\overline{CE}x \geq V \text{DD}$  0.2V means  $\overline{CE}\text{OX} \geq V \text{DD}$  0.2V or CE1X  $\leq$  0.2V
- "X" represents "L" for left port or "R" for right port.
- 6. 'X' in part number indicates power rating (S or L).



### High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAM

Industrial and Commercial Temperature Range

## AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

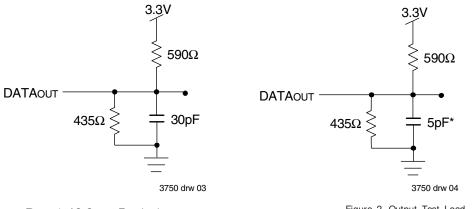
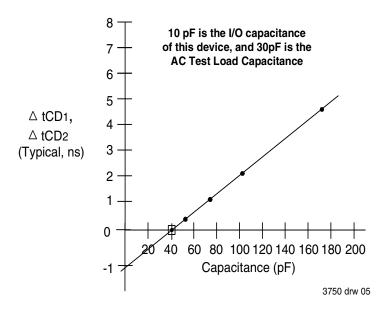


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tCKLZ, tCKHZ, tOLZ, and tOHZ). \*Including scope and jig.





High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAM

# AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)<sup>(3,4)</sup> (VDD = $3.3V \pm 0.3$ , TA = 0°C to +70°C)

(Read			89/79X6 'l Only	70V908	39/79X7 I Only	70V908	39/79X9 I Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) <sup>(2)</sup>	19	_	22	—	25		ns
tCYC2	Clock Cycle Time (Pipelined) <sup>(2)</sup>	10	_	12		15		ns
tCH1	Clock High Time (Flow-Through) <sup>(2)</sup>	6.5	_	7.5		12		ns
tCL1	Clock Low Time (Flow-Through) <sup>(2)</sup>	6.5	-	7.5		12		ns
tCH2	Clock High Time (Pipelined) <sup>(2)</sup>	4		5		6		ns
tCL2	Clock Low Time (Pipelined) <sup>(2)</sup>	4	_	5		6		ns
tR	Clock Rise Time		3		3		3	ns
tF	Clock Fall Time		3		3		3	ns
tsa	Address Setup Time	3.5		4		4		ns
tha	Address Hold Time	0		0		1		ns
tsc	Chip Enable Setup Time	3.5	_	4		4		ns
tнc	Chip Enable Hold Time	0		0		1		ns
tsw	R/W Setup Time	3.5	_	4		4		ns
tнw	R/W Hold Time	0	_	0		1		ns
tsp	Input Data Setup Time	3.5		4		4		ns
tнo	Input Data Hold Time	0		0		1		ns
tsad	ADS Setup Time	3.5		4		4		ns
thad	ADS Hold Time	0		0		1		ns
tscn	CNTEN Setup Time	3.5		4		4		ns
thon	CNTEN Hold Time	0		0		1		ns
tSRST	CNTRST Setup Time	3.5		4		4		ns
tHRST	CNTRST Hold Time	0		0		1		ns
toe	Output Enable to Data Valid		6.5		7.5		9	ns
tolz	Output Enable to Output Low-Z <sup>(1)</sup>	2		2		2		ns
toнz	Output Enable to Output High-Z <sup>(1)</sup>	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) <sup>(2)</sup>		15		18		20	ns
tCD2	Clock to Data Valid (Pipelined) <sup>(2)</sup>		6.5		7.5		9	ns
tDC	Data Output Hold After Clock High	2		2		2		ns
tскнz	Clock High to Output High-Z <sup>(1)</sup>	2	9	2	9	2	9	ns
tCKLZ	Clock High to Output Low-Z <sup>(1)</sup>	2		2		2		ns
Port-to-Port D	). Delay	-	-	-	-	-	-	
tCWDD	Write Port Clock High to Read Data Delay		24		28		35	ns
tccs	Clock-to-Clock Setup Time		9		10		15	ns

NOTES:

3750 tbl 11a

 Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

2. The Pipelined output parameters (tcvc1, tcD1) apply to either or both left and right ports when FT/PIPE = VIH. Flow-through parameters (tcvc1, tcD1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPE. FT/PIPE should be treated as a DC signal, i.e. steady state during operation.

4. 'X' in part number indicates power rating (S or L).

High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAM

# AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)<sup>(3,4)</sup> (VDD = $3.3V \pm 0.3$ )

			9/79X12 & Ind	70V908 Com	8979X15 'I Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) <sup>(2)</sup>	30		35	_	ns
tcyc2	Clock Cycle Time (Pipelined) <sup>(2)</sup>	20		25		ns
tсн1	Clock High Time (Flow-Through) <sup>(2)</sup>	12		12		ns
tCL1	Clock Low Time (Flow-Through) <sup>(2)</sup>	12		12	_	ns
tch2	Clock High Time (Pipelined) <sup>(2)</sup>	8		10	_	ns
tcl2	Clock Low Time (Pipelined) <sup>(2)</sup>	8		10		ns
tR	Clock Rise Time		3		3	ns
tF	Clock Fall Time		3		3	ns
tsa	Address Setup Time	4		4	-	ns
tна	Address Hold Time	1		1		ns
tsc	Chip Enable Setup Time	4		4	_	ns
tнc	Chip Enable Hold Time	1		1	_	ns
tsw	R/₩ Setup Time	4		4		ns
tнw	R/W Hold Time	1		1		ns
tsD	Input Data Setup Time	4		4	_	ns
tнD	Input Data Hold Time	1		1		ns
tsad	ADS Setup Time	4		4		ns
thad	ADS Hold Time	1		1		ns
tscn	CNTEN Setup Time	4		4		ns
thon	CNTEN Hold Time	1		1		ns
tSRST	CNTRST Setup Time	4		4		ns
thrst	CNTRST Hold Time	1		1		ns
toe	Output Enable to Data Valid		12		15	ns
tolz	Output Enable to Output Low-Z <sup>(1)</sup>	2		2		ns
toнz	Output Enable to Output High-Z <sup>(1)</sup>	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) <sup>(2)</sup>		25		30	ns
tCD2	Clock to Data Valid (Pipelined) <sup>(2)</sup>		12		15	ns
tDC	Data Output Hold After Clock High	2		2		ns
tскнz	Clock High to Output High-Z <sup>(1)</sup>	2	9	2	9	ns
tcklz	Clock High to Output Low-Z <sup>(1)</sup>	2		2		ns
Port-to-Port	- Delay	-	•	•	•	-
tcwdd	Write Port Clock High to Read Data Delay		40		50	ns
tccs	Clock-to-Clock Setup Time		15		20	ns

3750 tbl 11b

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

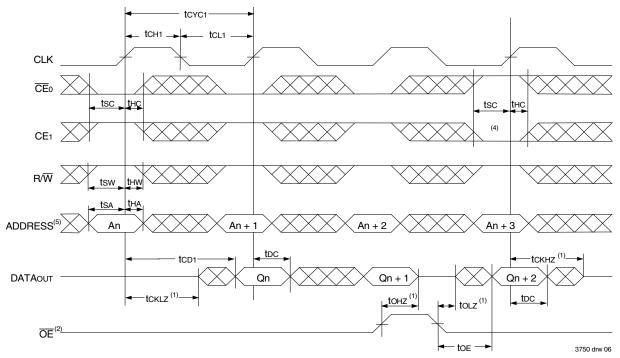
This parameter is guaranteed by device characterization, but is not production tested.

2. The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when FT/PIPE = VIH. Flow-through parameters (tcvc1, tcb1) apply when FT/PIPE = VIL for that port.

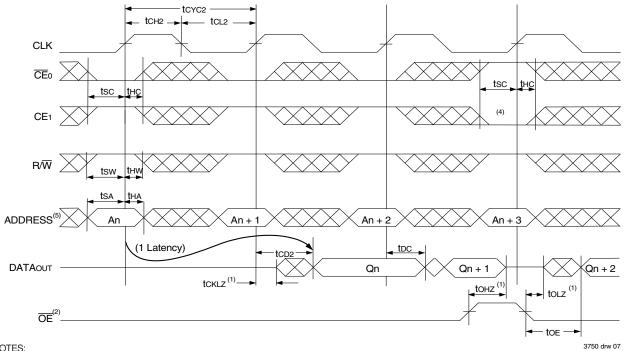
3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPE. FT/PIPE should be treated as a DC signal, i.e. steady state during operation.

4. 'X' in part number indicates power rating (S or L).

# Timing Waveform of Read Cycle for Flow-Through Output $(\mathbf{FT}/PIPE^{*}x^{*} = VIL)^{(3,6)}$



Timing Waveform of Read Cycle for Pipelined Output ( $\overline{FT}$ /PIPE"x" = VIH)<sup>(3,6)</sup>



NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

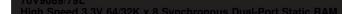
2. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.

3.  $\overline{ADS} = VIL$  and  $\overline{CNTRST} = VIH$ .

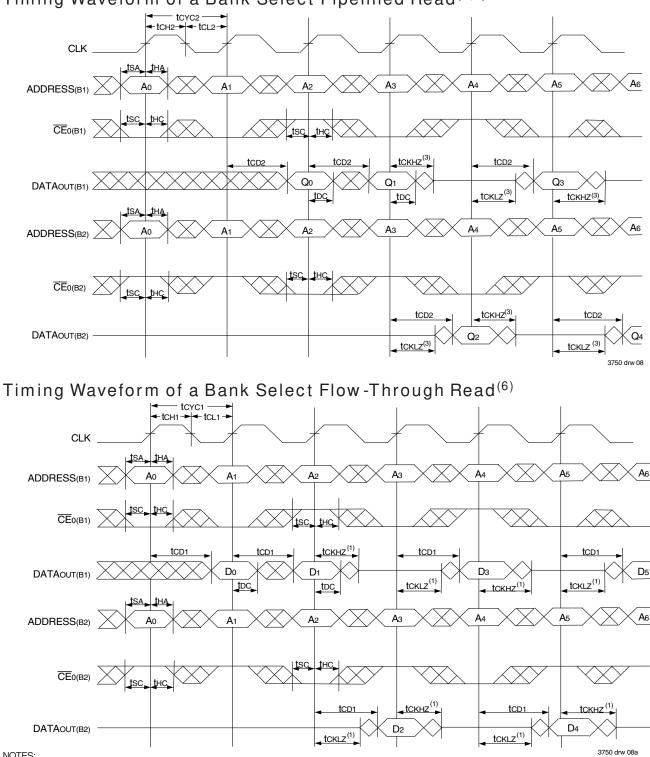
4. The output is disabled (High-impedance state) by  $\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}$  following the next rising edge of clock. Refer to Truth Table 1.

5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for

reference use only. 6. "x" denotes Left or Right port. The diagram is with respect to that port.



## Timing Waveform of a Bank Select Pipelined Read<sup>(1,2)</sup>

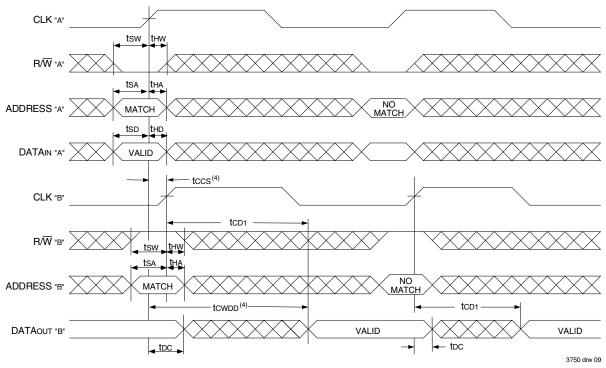


- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9089/79 for this waveform,
- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2.  $\overline{OE}$  and  $\overline{ADS}$  = VIL; CE1(B1), CE1(B2), R/W and  $\overline{CNTRST}$  = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4.  $\overline{CE}_0$  and  $\overline{ADS} = VIL$ ; CE1 and  $\overline{CNTRST} = VIH$ .
- 5.  $\overline{OE} = V_{IL}$  for the Right Port, which is being read from.  $\overline{OE} = V_{IH}$  for the Left Port, which is being written to.
- 6. If tccs < maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.

High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RA

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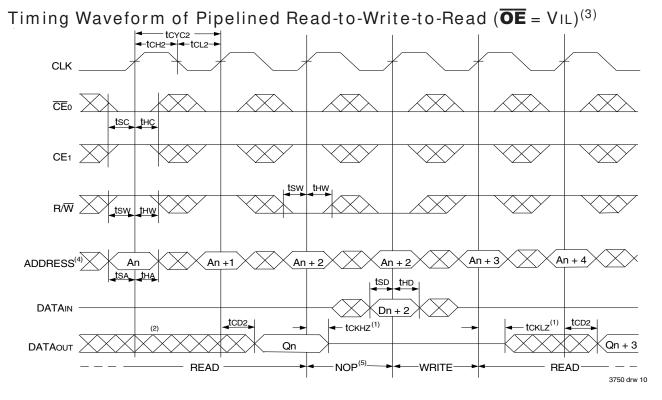
Timing Waveform Port-to-Port Flow -Through Read<sup>(1,2,3,5)</sup>



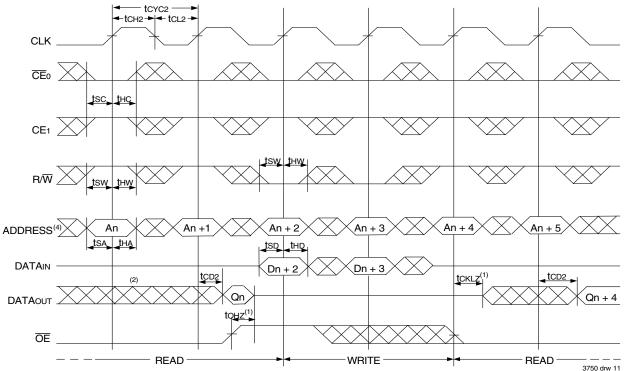
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2.  $\overline{CE}_0$  and  $\overline{ADS} = VIL$ ; CE1 and  $\overline{CNTRST} = VIH$ .
- 3.  $\overline{OE}$  = VIL for the Port "B", which is being read from.  $\overline{OE}$  = VIH for the Port "A", which is being written to.
- 4. If tccs < maximum specified, then data from right port READ is not valid until the maximum specified for tcwpd.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.
- 5. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

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Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)(3)



### NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

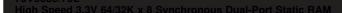
2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

3.  $\overline{CE}_0$  and  $\overline{ADS} = V_{IL}$ ; CE1 and  $\overline{CNTRST} = V_{IH}$ .

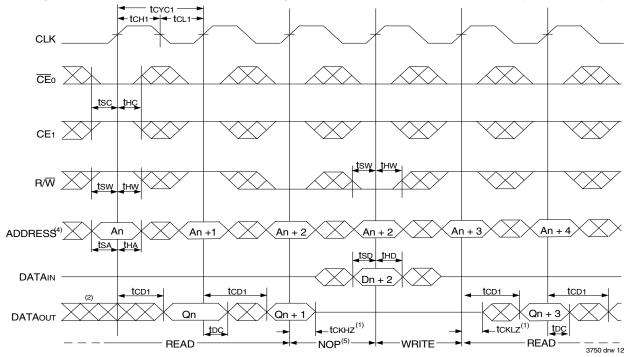
4. Addresses do not have to be accessed sequentially since ADS = VL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

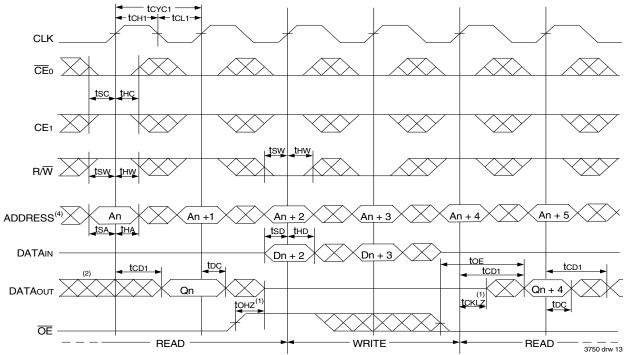




Timing Waveform of Flow-Through Read-to-Write-to-Read  $(\overline{OE} = VIL)^{(3)}$ 



Timing Waveform of Flow -Through Read-to-Write-to-Read (**OE** Controlled)<sup>(3)</sup>



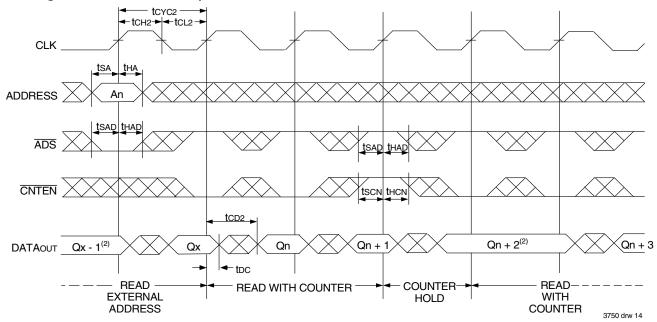
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3.  $\overline{CE}_0$  and  $\overline{ADS} = VIL$ ; CE1 and  $\overline{CNTRST} = VIH$ .
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.



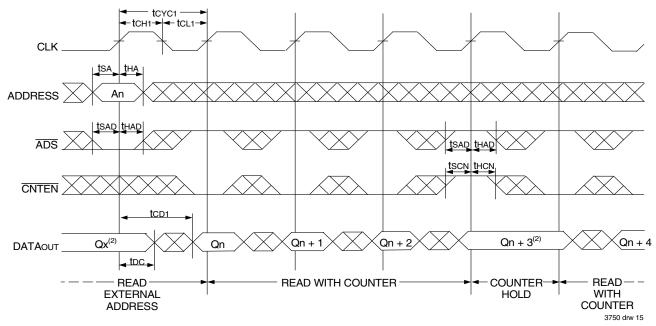
High Speed 3 3V 64/32K x 8 Synchronous Dual-Port Static BAN

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Timing Waveform of Pipelined Read with Address Counter Advance<sup>(1)</sup>



Timing Waveform of Flow -Through Counter Read with Address Counter Advance<sup>(1)</sup>

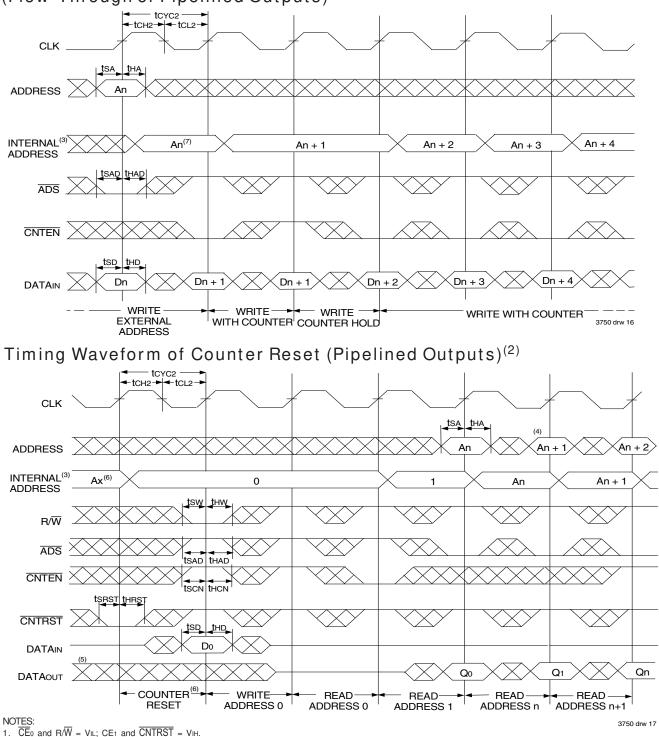


NOTES:

1.  $\overline{CE}_0$  and  $\overline{OE}$  = VIL; CE1, R/ $\overline{W}$ , and  $\overline{CNTRST}$  = VIH.

2. If there is no address change via  $\overline{\text{ADS}}$  = ViL (loading a new address) or  $\overline{\text{CNTEN}}$  = ViL (advancing the address), i.e.  $\overline{\text{ADS}}$  = ViH and  $\overline{\text{CNTEN}}$  = ViH, then the data output remains constant for subsequent clocks.

## Timing Waveform of Write with Address Counter Advance (Flow -Through or Pipelined Outputs)<sup>(1)</sup>



- 2.  $\overline{CE}_0 = VIL; CE_1 = VIH.$
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = VL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset. ADDR0 will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' address is written to during this cycle.

### High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAM

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### **Functional Description**

The IDT70V9089/79 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the counter registers for fast interleaved memory applications.

A HIGH on  $\overline{CE}_0$  or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9089/79's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with  $\overline{CE}_0$  LOW and CE1 HIGH to reactivate the outputs.

### Depth and Width Expansion

The IDT70V9089/79 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V9089/79 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 16-bit or wider applications.

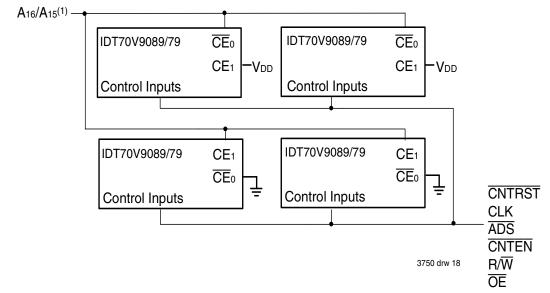


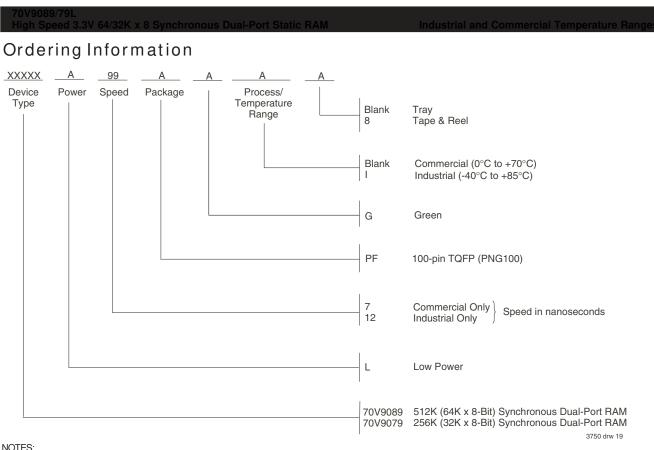
Figure 4. Depth and Width Expansion with IDT70V9089/79

### NOTE:

1. A16 is for IDT70V9089. A15 is for IDT70V9079.

### IDT Clock Solution for IDT70V9089/79 Dual-Port

		Dual-Port I/O Specitications		Clock Specifications				IDT	IDT
IDT Dual-Port Part Number	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement	Maximum Frequency	Jitter Tolerance	PLL Clock Device	Non-PLL Clock Device	
70V9089	9/79	3.3	LVTTL	9pF	40%	100	150ps	2305 2308 2309	49FCT3805 49FCT3805D/E 74FCT3807 74FCT3807D/E



### NOTES:

LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02

Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

## Ordering Information for Flow -through Devices

Old Flow-through Part	New Combined Part		
70V908S/L25	70V9089L12		
	3750 tbl 12		
Old Flow-through Part	New Combined Part		
70V907S/L25	70V9079L7		

## Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
7	70V9079L7PFG8	PNG100	TQFP	С
	70V9079L7PFG	PNG100	TQFP	С

	Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
ſ	12	70V9089L12PFGI	PNG100	TQFP	Ι
		70V9089L12PFGI8	PNG100	TQFP	I

### Datasheet Document History

01/18/99:

Initiated datasheet document history Converted to new format Cosmetic and typographical corrections Added additional notes to pin configurations Added Depth and Width Expansion section.

Page 14

### High Speed 3.3V 64/32K x 8 Synchronous Dual-Port Static RAM

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## Datasheet Document History (con't.)

06/11/99:	Page 3	Deleted note 6 for Table II
11/12/99:	C C	Replaced IDT logo
03/31/00:		Combined Pipelined 70V9089 family and Flow-through 70V908 family offerings into one data sheet
		Changed ±200mV in waveform notes to 0mV
		Added corresponding part chart with ordering information
01/10/01:	Page 3	Changed information in Truth Table II
	Page 4	Increased storage temperature parameters
	0	Clarified TA parameter
	Page 5	DC Electrical parameters–changed wording from "open" to "disabled"
	0	Removed Preliminary Status
01/15/04:		Consolidated multiple devices into one datasheet
		Changed naming conventions from VCC to VDD and from GND to Vss
		Removed I-temp footnote from tables
	Page 2	Added date revision to pin configuration
	Page 4	Added Junction Temperature to Absolute Maximum Ratings Table
		Added Ambient Temperature footnote
	Page 5	Added I-temp numbers for 9ns speed to the DC Electrical Characteristics Table
		Added 6ns & 7ns speeds DC power numbers to the DC Electrical Characteristics Table
	Page 7	Added I-temp for 9ns speed to AC Electrical Characteristics Table
	0	Added 6ns & 7ns speeds AC timing numbers to the AC Electrical Characteristics Table
	Page 16	Added 6ns & 7ns speeds grade and 9ns I-temp to ordering information
	C C	Added IDT Clock Solution Table
	Pages 1 & 17	Replaced <sup>®</sup> IDT logo with ™ new logo
05/11/04:	Pages 1 & 19	Added 7ns speed grade to ordering information
	Page 5	Added 7ns speed DC power numbers to the DC Electrical Characteristics Table
	Page 8	Added 7ns speed AC timing numbers to the AC Electrical Characteristics Table
12/01/05:	Page 1	Added green parts availability to features
	Page 18	Added green indicator to ordering information
01/19/09:	Page 18	Removed "IDT" from orderable part number
07/26/10:	Page 8	In order to correct the header notes of the AC Elect Chars Table and align them with the Industrial temp range
		values located in the table, the commercial TA header note has been removed
	Pages 10-14	In order to correct the footnotes of timing diagrams, CNTEN has been removed to reconcile the footnotes with
		the CNTEN logic definition found in Truth Table II - Address Counter Control
07/15/14:	Page 1	Replaced Industrial 9ns with 12ns. Replaced Low Power Operation Standby from 600mW (typ) to
		1.32mW (typ) in the Features
	Page 2	Corrected some text typos
	Page 5	Removed the 9ns Industrial temp power values for the S & L offering in the DC Elec Chars table
	Page 6	Added the 12ns Industrial temp power value for the L offering in the DC Elec Chars table
	Pages 8 & 9	Updated the column headings of the AC Elec Chars table to indicate the Commercial and Industrial speed grade offerings
	Page 18	Updated all the Commercial and Industrial speed grade offerings and added
		Tape & Reel to Ordering Information
	Page 2 & 18	The label PN100-1 changed to PN100 to match the standard package code
	Page 18	Corrected Old Flow-through Part number in table 13 to 70V907S/L25 & S/L30
02/20/18:	0 -	Product Discontinuation Notice - PDN# SP-17-02
		Last time buy expires June 15, 2018
09/25/19:	Page 1 & 18	Deleted obsolete Commercial speed grades 6/9/12/15ns in Features and Ordering Information
	Page 2	Rotated PNG100 TQFP pin configuration to accurately reflect pin 1 orientation
	Page 18	Added Orderable Part Information table

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